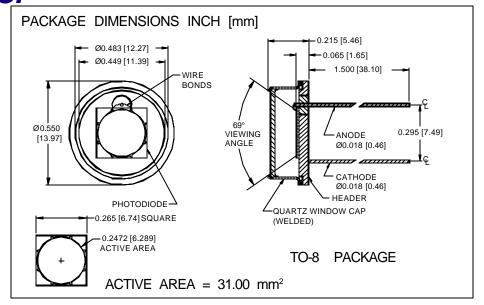
PHOTONIC Silicon Photodiode, U.V. Enhanced Photoconductive DETECTORS INC. Type PDU-C108-Q





FEATURES

- High speed
- U.V. enhanced
- Low capacitance
- Quartz window

DESCRIPTION

The **PDU-C108-Q** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a TO-8 metal can with a flat quartz window.

APPLICATIONS

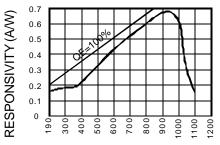
- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		30	V
T _{STG}	Storage Temperature	-55	+150	∞
То	Operating Temperature Range	-40	+125	∞
Ts	Soldering Temperature*		+240	∞
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	400	460		μΑ
ΙD	Dark Current	H = 0, V _R = 5 V		5	15	pA
RsH	Shunt Resistance	H = 0, V _R = 10 mV	32	60		MΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
Cı	Junction Capacitance	$H = 0$, $V_R = 5 V^{**}$		350		рF
λrange	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	$V_{R} = 0 \text{ V}, \ \lambda = 254 \text{ nm}$.12	.18		A/W
VBR	Breakdown Voltage	Ι = 10 μΑ	15	25		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		4x10 ⁻¹⁴		W/√Hz
tr	Response Time	$RL = 1 K\Omega V_R = 5 V$		110		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz